Jae Hyun Kim
Principal Engineer,
Semiconductor Business, Samsung Electronics Co. Ltd.

JAE HYUN KIM

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EDUCATION

SEOUL NATIONAL UNIVERSITY, Seoul, Korea Ph.D. *in Chemical Engineering, Aug. 2000.*
Thesis entitled "Surface Characteristics and Physical Properties of Various Polymer Films"
POHANG UNIVERSITY OF SCIENCE AND TECHNOLOGY, Pohang, Korea, M.S. *in Material Science and Engineering, Feb. 1997.*
Thesis entitled "Thickness Dependence of the Glass Transition Temperature of Thin Polymer Films"
INHA UNIVERSITY, Incheon, Korea, B.S. *in Polymer Science and Technology, Feb. 1995.*

MAJOR RESPONSIBILITY

Present **SAMSUNG ELECTRONICS**, SEMICONDUTOR DIVISION, Hwasung, Korea
Principal Engineer

- Leading the lithographic material development group
- Building the lithography strategy and running material selection decision board
- Design and develop the novel material for the smaller device with global chemical suppliers
- Manufacturing cost reduction strategy development
- Quality control system development for the incoming materials
- Audit the quality control system of the major material suppliers and upgrade the suppliers' manufacturing system
- Assess new business opportunity and develop business strategy in electronic material industry
- Incubate new material suppliers by assigning target requirements and jointly engineering programs

MAJOR TECHNICAL ACHIEVEMENETS

2010	Lithography productivity enhancement by developing interchangeable process
2009	Immersion specific photoresist development, ArFi scanner productivity improvement
2008	Localization of the major lithography materials and incubating local material companies
2006	Stabilization of immersion lithography process by new material and process development
2005	Member of 512M DRAM development with 106nm process
2003	Member of 12inch wafer handling fabrication line design for lithography process
2002	Photosensitive Polyimide buffer coating process development and adaptation in mass production
2001	Lithography engineer at 146nm node size process development for 128M DRAM

ADDITIONAL INFORMATION

- Author of International Scientific Paper : 23 Papers
- Author of USA Patent : 5 Patents